MMDT2222A

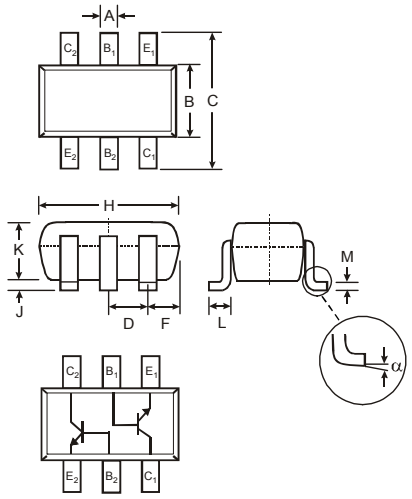
DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMDT2907A)
- **Lead Free/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3 and 4)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe)
- Terminal Connections: See Diagram
- Marking Information: K1P, See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I_C	600	mA
Total Power Dissipation (Note 1)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. No purposefully added lead.
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	75	—	V	I_C = 10μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	I_C = 10mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	I_E = 10μA, I_C = 0
Collector Cutoff Current	I_{CBO}	—	10	nA μA	V_{CB} = 60V, I_E = 0 V_{CB} = 60V, I_E = 0, T_A = 150°C
Collector Cutoff Current	I_{CEX}	—	10	nA	V_{CE} = 60V, $V_{EB(OFF)}$ = 3.0V
Emitter Cutoff Current	I_{EBO}	—	10	nA	V_{EB} = 3.0V, I_C = 0
Base Cutoff Current	I_{BL}	—	20	nA	V_{CE} = 60V, $V_{EB(OFF)}$ = 3.0V
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h_{FE}	35 50 75 100 40 50 35	— — — 300 — — —	—	I_C = 100μA, V_{CE} = 10V I_C = 1.0mA, V_{CE} = 10V I_C = 10mA, V_{CE} = 10V I_C = 150mA, V_{CE} = 10V I_C = 500mA, V_{CE} = 10V I_C = 10mA, V_{CE} = 10V, T_A = -55°C I_C = 150mA, V_{CE} = 1.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.3 1.0	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.6 —	1.2 2.0	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	8	pF	V_{CB} = 10V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	25	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = 20V, I_C = 20mA, f = 100MHz
Noise Figure	NF	—	4.0	dB	V_{CE} = 10V, I_C = 100μA, R_S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	10	ns	V_{CC} = 30V, I_C = 150mA, $V_{BE(off)}$ = - 0.5V, I_{B1} = 15mA
Rise Time	t_r	—	25	ns	
Storage Time	t_s	—	225	ns	V_{CC} = 30V, I_C = 150mA, I_{B1} = I_{B2} = 15mA
Fall Time	t_f	—	60	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.

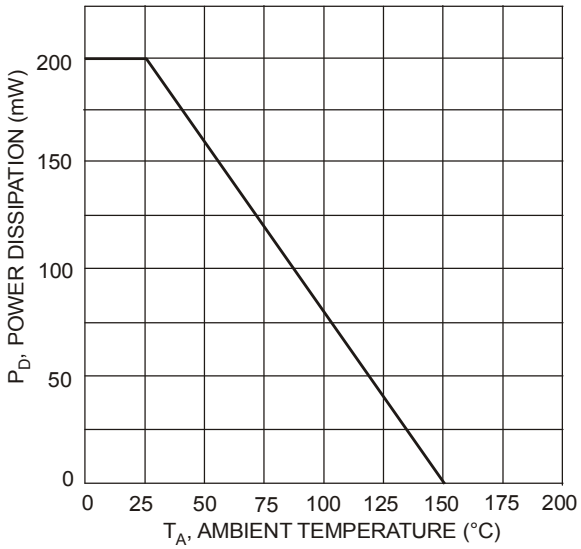


Fig. 1, Max Power Dissipation vs. Ambient Temperature

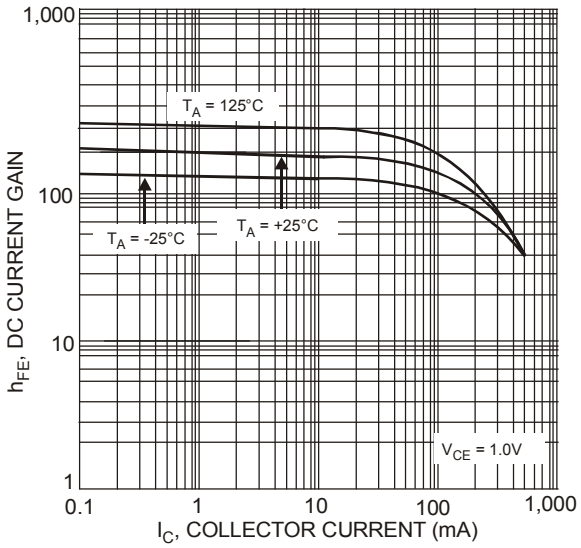


Fig. 2, Typical DC Current Gain vs. Collector Current

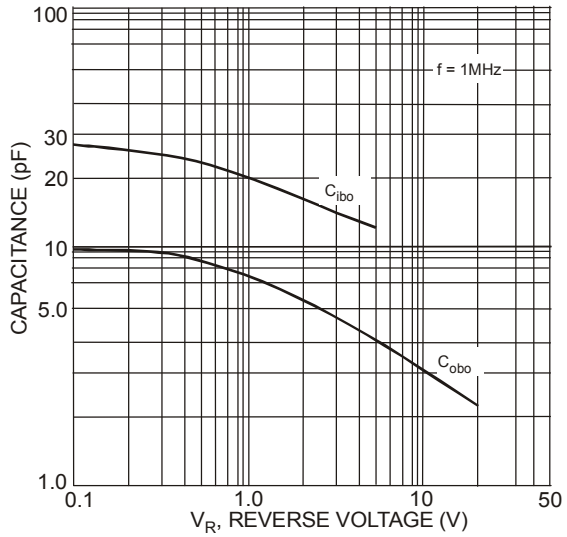


Fig. 3, Typical Capacitance Characteristics

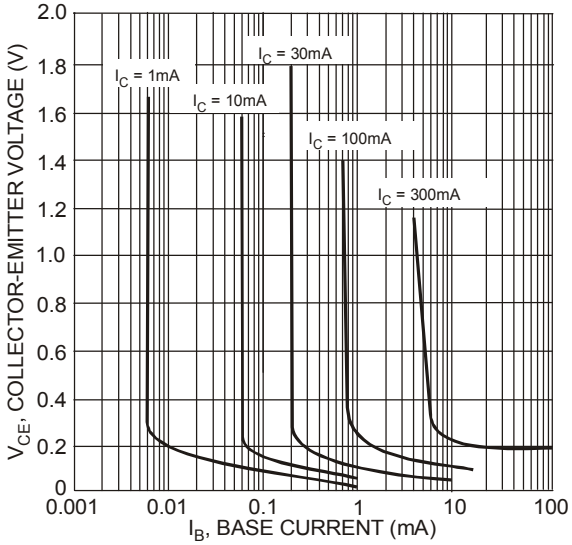


Fig. 4, Typical Collector Saturation Region

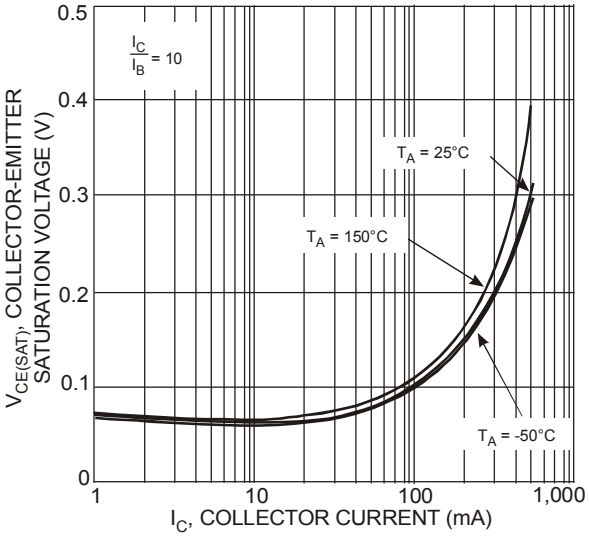


Fig. 5, Typical Collector-Emitter Saturation Voltage vs. Collector Current

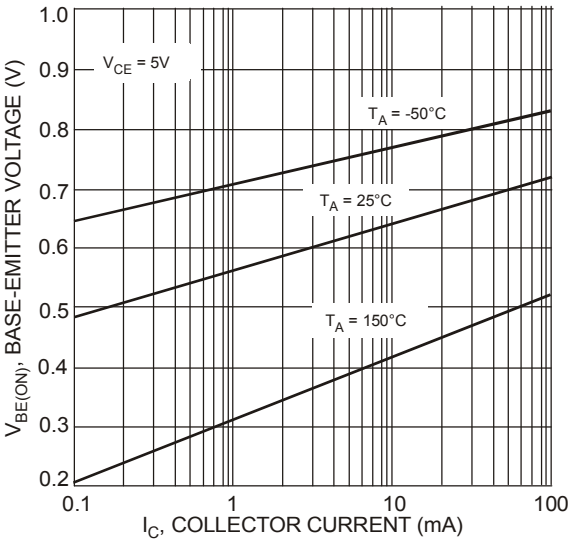


Fig. 6, Typical Base-Emitter Voltage vs. Collector Current

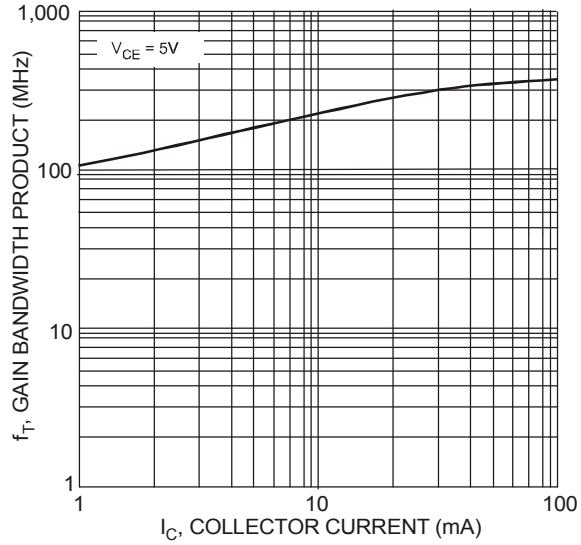


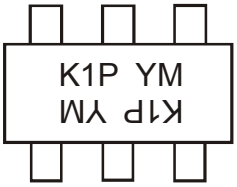
Fig. 7, Typical Gain Bandwidth Product vs. Collector Current

Ordering Information (Note 6)

Device	Packaging	Shipping
MMDT2222A-7-F	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K1P = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D